# Inkjet Printed BST Thick-Films for X-Band Phase Shifter and Phased Array Applications



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Motivation	Antennas	$\bigtriangledown$	Ferroelectric material:							
<ul> <li>The phased array antenna consists of:</li> <li>Feeding network</li> </ul>	Phase Shifters	$( \phi)$	$\bigcirc$	$( \phi)$	Ø	Ø	$( \phi)$	Ø	Ø	Barium-Strontium-Titanate (BST) <ul> <li>Low power consumption</li> </ul>
<ul><li>Phase shifters</li><li>Antennas</li></ul>	Feeding Lines							]		<ul> <li>High tuning speed</li> <li>High linearity</li> </ul>
	Transmitters/Receiver						er		• Adequate dielectric loss	

- System performance is depended on the insertion loss of the feeding network and the phase shifters
- A tunable compact phase shifter can reduce the total size
- The kernel elements in the phase shifters are varactors
- Different technologies to fabricate tunable varactors: semiconductor, MEMS, ferroelectric, liquid crystal and ferrite

## Inkjet Printing of BST

#### Inkjet printing technology:

- Selective printing of BST material
- Flexible fabrication process
- Simultaneous multi material printing option
- Single nozzle printhead with 100µm orifice diameter



#### **BST material Characterization by IDC**

- Interdigital capacitors (IDC) measured by on-wafer probes
- The permittivity of the material changes from 220 (0V) to 140 (200V)
- By applying 20 V/µm a maximum tunability is 35%



### Simulation & Measurement

#### Simulation:

- The phase shifter designed for the frequency range of 8-10 GHz
- Agilent ADS simulation tool is used
- The tunable capacitors are designed on a substrate consisting of BST layer on top of an aluminum oxide substrate
- The permittivity of the BST layer changes between 220 to 140
- The gap width of the capacitors is 10µm
- Insertion loss decreases with the change in permittivity
- The transmitted phase can be tuned continuously

#### **On-Wafer measurements results:**

- Measurement in a 50  $\Omega$  system
- Tuning voltage applied by using Bias-T
- Tuning Voltage changed between 0 to 200 V
- The achieved phase shift at 10 GHz was 175° with a FoM of 20°/dB
- Higher losses than expected









#### Phase Shifter Realization

- Single photolithography process
- Top electrode: 2µm Gold by electroplating
- The BST strips have a thickness of 2.1µm and width of 300µm on top of an aluminum oxide with 635µm thickness
- •The BST thick-film is printed at the areas beneath the interdigital capacitors
- Each phase shifter has 9 unit cells, each unit consist of two tunable capacitors
- The capacitance of the first unit cell at the input and output were chosen Conclusion smaller for better matching

#### Inkjet printing BST thick-film



• A new method for tunable microwave components Realization of a loaded line phase shifter

• The fabricated prototype exhibits a compact size (8mm × 6mm) • Low current consumption (less than 0.1mA)

#### **Further Work**

- Increase FoM
- Loss factor of the BST has to be reduced
- Using metal-insulator-metal capacitors
- Reduce the biasing voltage
- Increase the tunability



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